



US 20230231017A1

(19) **United States**

(12) **Patent Application Publication**
ISHIBASHI et al.

(10) **Pub. No.: US 2023/0231017 A1**

(43) **Pub. Date: Jul. 20, 2023**

(54) **SEMICONDUCTOR DEVICE AND POWER
CONVERSION APPARATUS**

(52) **U.S. Cl.**
CPC *H01L 29/1608* (2013.01); *H01L 29/0696*
(2013.01); *H01L 29/7804* (2013.01)

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(21) Appl. No.: **18/051,432**

(22) Filed: **Oct. 31, 2022**

(30) **Foreign Application Priority Data**

Jan. 19, 2022 (JP) 2022-006132

Publication Classification

(51) **Int. Cl.**
H01L 29/16 (2006.01)
H01L 29/06 (2006.01)
H01L 29/78 (2006.01)

(57) **ABSTRACT**

A semiconductor device has a cell region, a dividing region dividing the cell region in an expanding direction of a stacking fault band, and a termination region, and includes in a dividing region, a semiconductor layer including a drift region of a first conductivity type and a second well region of a second conductivity type provided in an upper portion of the drift region, a second interlayer insulating film provided on the semiconductor layer, and a source electrode provided on the second interlayer insulating film. The second interlayer insulating film has two second contact holes aligned in an expanding direction of stacking fault band and electrically connecting the source electrode to the second well region. The second well region is formed as one region continuous in the expanding direction of stacking fault band in the region interposed between the two second contact holes in top view.

